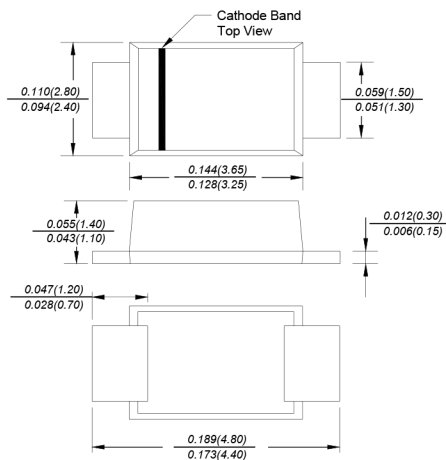


US1AF THRU US1MF

SURFACE MOUNT ULTRA FAST RECTIFIER
 Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

SMAF



FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Ultra fast switching for high efficiency
- ◆ Low reverse leakage
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed 260°C/10 seconds at terminals
- ◆ Glass passivated chip junction

MECHANICAL DATA

Case: JEDEC SMAF molded plastic body over passivated chip
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.0018 ounce, 0.064 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

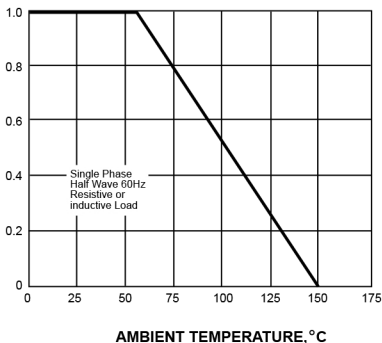
MDD Catalog Number	SYMBOLS	US1AF	US1BF	US1DF	US1GF	US1JF	US1KF	US1MF	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_L=55^\circ\text{C}$	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.0		1.4	1.7			Volts	
Maximum DC reverse current at rated DC blocking voltage $T_A=25^\circ\text{C}$ $T_A=100^\circ\text{C}$	I_R	5.0 50.0							μA
Maximum reverse recovery time (NOTE 1)	t_{rr}	50				75			ns
Typical junction capacitance (NOTE 2)	C_J	15.0							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	50.0							$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{STG}	-50 to +150							$^\circ\text{C}$

Note: 1. Reverse recovery condition $I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES US1AF THRU US1MF

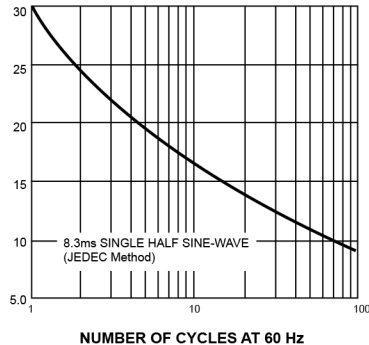
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



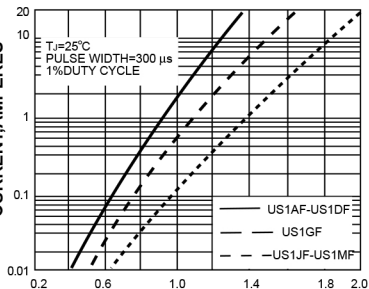
PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



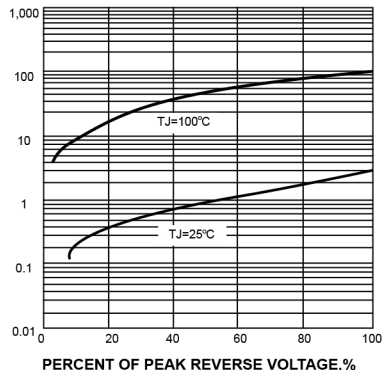
INSTANTANEOUS FORWARD CURRENT, AMPERES

FIG. 3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



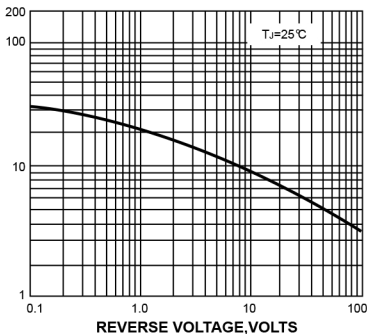
INSTANTANEOUS REVERSE CURRENT,
MICROAMPERES

FIG. 4- TYPICAL REVERSE CHARACTERISTICS



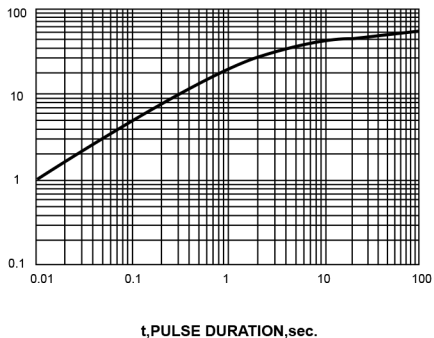
JUNCTION CAPACITANCE, pF

FIG. 5- TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE,
°C/W

FIG. 6- TYPICAL TRANSIENT THERMAL IMPEDANCE



单击下面可查看定价，库存，交付和生命周期等信息

[>>RCD\(达标电子\)](#)